

IN THE CLAIMS

1-12. (*Canceled*).

13. (*Previously Presented*) A method for megasonic cleaning of semiconductor wafers comprising the steps of:

generating two or more parallel sets of megasonic waves in a cleaning fluid, the megasonic waves having a direction of travel and wave fronts that are
5 generally perpendicular to the direction of travel;

immersing semiconductors in the cleaning fluid; and

moving the wafers in the cleaning fluid through said megasonic waves in a direction that is generally perpendicular to the direction of travel of the megasonic waves and generally perpendicular to the wave fronts of the megasonic waves.

14. (*Original*) The method of claim 13 wherein the megasonic waves are generated across parallel regions of the fluid and the step of moving the wafers comprises reciprocating the wafers through said parallel regions.

15. (*Currently Amended*) A method for megasonic cleaning of semiconductor wafers disposed ~~at least partially~~ within a holder, the holder and

wafers disposed ~~at least partially~~ in a cleaning fluid within a container, the method comprising the steps of:

- 5 generating megasonic waves in the cleaning fluid;
 intercepting the generated waves inside the container at a location
between one or more sources of the megasonic waves and the holder, and
dispersing the waves in a divergent manner; and
 exposing the semiconductor wafers to the dispersed megasonic waves
10 within the cleaning fluid.

16-26. *(Canceled)*.

27. *(Previously Presented)* A method for megasonic cleaning of semiconductor wafers comprising the steps of:

- generating two or more parallel sets of megasonic waves in a cleaning
fluid;
5 immersing semiconductors in the cleaning fluid; and
 moving the wafers in the cleaning fluid through said megasonic waves in a
direction that is generally transverse to the megasonic waves and generally
perpendicular to faces of the wafers.